

## HIGH EFFICIENCY GLASS PASSIVATED RECTIFIER HER801G ~ HER808G

# **High Efficiency Glass Passivated Rectifier**

#### Features

- Glass passivated chip junction
- Low power loss, high efficiency
- Low leakage
- High Surge Capacity
- High switching speed
- High temperature soldering guaranteed:
- 260  $^\circ\mathrm{C}/10$  seconds, 0.375" (9.5mm) lead length from case
- Also available in reverse polarity, add the "R" Suffix, i.e. HER801GR
- Also available in isolated package under part number HERF801G
- RoHS and REACH Compliance

### **Mechanical Data**

Case:	Transfer molded plastic
Polarity:	Color band denots cathode end
Ероху:	UL94V-0 rate flame retardant
Lead:	Plated axial lead, solderable per MIL-STD-202E Method 208C
Mounting Position:	Any
Weight:	0.064 ounce, 1.81 gram

#### Maximum Ratings (T Ambient=25°C unless noted otherwise)

Symbol	Description		HER 802G	HER 803G	HER 804G	HER 805G	HER 806G	HER 807G	HER 808G	Unit	Conditions
VRRM	Max Recurrent Peak Reverse Voltage		100	200	300	400	600	800	1000	v	
VRMS	Max RMS Voltage	35	70	140	210	280	420	560	700	v	
VDC	Max DC Blocking Voltage	50	100	200	300	400	600	800	1000	v	
I(AV)	Max Average Forward Rectified Current 0.375" (9mm) lead length	8.0								А	Tc=75℃
IFSM	Peak Forward Surge Current	200							Α	JEDEC method	
TJ,TSTG	Operating and Storage Temperature Range	-55 to +150, -55 to +150							C		

## Electrical Characteristics (T Ambient=25°C unless noted otherwise)

Symbol	Description	HER 801G	HER 802G	HER 803G	HER 804G	HER 805G	HER 806G	HER 807G	HER 808G	Unit	Conditions
VF	Max Instantaneous Forward Voltage	1.0	)	1.3		1.5		1.7		v	8.0A
Rθ-JA	Typical Thermal Resistance		10								Note 2
IR	Max DC Reverse Current at Rated DC Blocking Voltage	10 150								μA	TA=25℃ TA=125℃
TRR	Maximum reverse recovery time	50 70							nS	Note 1	
C	Typical Junction capacitance	110							pF	Measured at 1.0MHz / 4.0V	

Note:

1. Reverse recovery test conditions: IF= 0.5A, IR=1.0A, IRR = 0.25A

2. Unit mounted on heatsink





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## **RATINGS AND CHARACTERISTIC CURVES HER801G THRU HER808G**

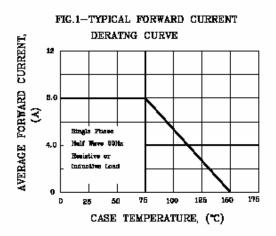


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

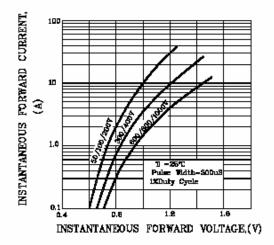
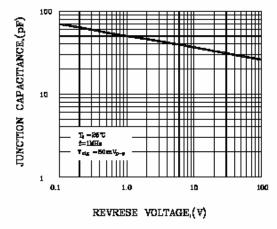
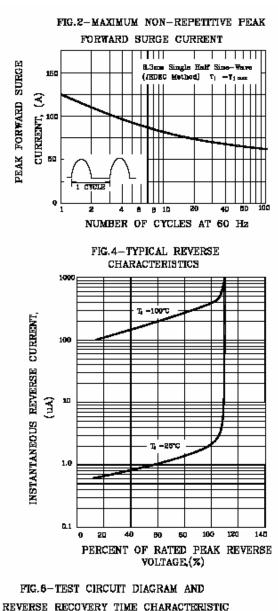
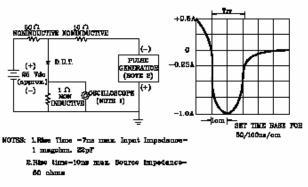


FIG.5-TYPICAL JUNCTION CAPACITANCE



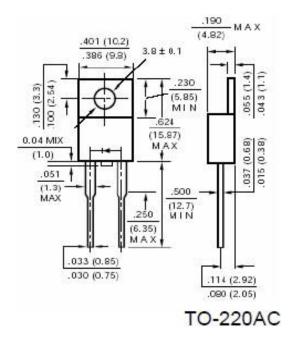






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## **Dimensions in inches (mm)**



Contact us:

## **US HEADQUARTERS**

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